SEMICONDUCTOR

## Unbuffered Inverter

## MC74VHC1GU04

The MC74VHC1GU04 is an advanced high speed CMOS Unbuffered inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This device consists of a single unbuffered inverter. In combination with others, or in the MC74VHCU04 Hex Unbuffered Inverter, these devices are well suited for use as oscillators, pulse shapers, and in many other applications requiring a high-input impedance amplifier. For digital applications, the MC74VHC1G04 or the MC74VHC04 are recommended.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.
The MC74VHC1GU04 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GU04 to be used to interface 5 V circuits to 3 V circuits.

- High Speed: $t_{p d}=2.5 \mathrm{~ns}(\mathrm{Typ})$ at $\mathrm{V}_{\mathrm{cc}}=5 \mathrm{~V}$
- Low Power Dissipation: $I_{c c}=2 \mathrm{~mA}(\operatorname{Max})$ at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 105; Equivalent Gates = 26


| PIN ASSIGNMENT |  |
| :---: | :---: |
| 1 | NC |
| 2 | IN A |
| 3 | GND |
| 4 | OUT $\overline{\mathrm{Y}}$ |
| 5 | $\mathrm{~V}_{\mathrm{cc}}$ |

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

SEMICONDUCTOR

MC74VHC1GU04

## MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {cc }}$ | DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{V}_{\text {IN }}$ | DC Input Voltage | -0.5 to +7.0 | V |
| V out | DC Output Voltage $\mathrm{V}_{\mathrm{cc}}=0$ | -0.5 to +7.0 | V |
|  | High or Low State | -0.5 to V cc +0.5 |  |
| $\mathrm{I}_{\text {IK }}$ | Input Diode Current | -20 | mA |
| I ок | Output Diode Current $\quad \mathrm{V}_{\text {out }}<\mathrm{GND} ; \mathrm{V}_{\text {out }}>\mathrm{V}_{\text {cc }}$ | +20 | mA |
| I out | DC Output Current, per Pin | +25 | mA |
| $\mathrm{I}_{\text {cc }}$ | DC Supply Current, $\mathrm{V}_{\text {cc }}$ and GND | +50 | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Power dissipation in still air SC-88A, TSOP-5 | 200 | mW |
| $\theta_{\text {JA }}$ | Thermal resistance SC-88A, TSOP-5 | 333 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 s | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{J}$ | Junction Temperature Under Bias | + 150 | ${ }^{\circ} \mathrm{C}$ |
| T stg | Storage temperature | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{V}_{\text {ESD }}$ | ESD Withstand Voltage Human Body Model (Note 2) | >2000 | V |
|  | Machine Model (Note 3) | > 200 |  |
|  | Charged Device Model (Note 4) | N/A |  |
| $\mathrm{I}_{\text {LATCH-Up }}$ | Latch-Up Performance Above $\mathrm{V}_{\text {cc }}$ and Below GND at $125^{\circ} \mathrm{C}$ (Note 5) | $\pm 500$ | mA |

1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.
2. Tested to EIA/JESD22-A114-A
3. Tested to EIA/JESD22-A115-A
4. Tested to JESD22-C101-A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {cc }}$ | DC Supply Voltage |  | 2.0 | 5.5 | V |
| $\mathrm{V}_{\text {in }}$ | DC Input Voltage |  | 0.0 | 5.5 | V |
| $\mathrm{V}_{\text {OUT }}$ | DC Output Voltage |  | 0.0 | V cc | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  | -55 | + 125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time | $\begin{aligned} & \mathrm{V}_{\mathrm{cc}}=3.3 \pm 0.3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{cc}}=5.0 \pm 0.5 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & 0 \\ & 0 \end{aligned}$ | No Limit No Limit | ns/V |

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1\% BOND FAILURES

| Junction <br> Temperature ${ }^{\circ} \mathrm{C}$ | Time, <br> Hours | Time, <br> Years |
| :---: | :---: | :---: |
| 80 | $1,032,200$ | 117.8 |
| 90 | 419,300 | 47.9 |
| 100 | 178,700 | 20.4 |
| 110 | 79,600 | 9.4 |
| 120 | 37,000 | 4.2 |
| 130 | 17,800 | 2.0 |
| 140 | 8,900 | 1.0 |



Figure 3. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Test Conditions | $\begin{aligned} & \mathrm{V}_{\mathrm{cc}} \\ & \text { (V) } \\ & \hline \end{aligned}$ | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $\mathrm{T}_{\mathrm{A}} \leq 85^{\circ} \mathrm{C}$ |  | $-55^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 125^{\circ} \mathrm{C}$ |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max | Min | Max | Min | Max |  |
| $\mathrm{V}_{\text {H }}$ | Minimum High-Level |  | 2.0 | 1.7 |  |  | 1.7 |  | 1.7 |  | V |
|  | Input Voltage |  | 3.0 | 2.4 |  |  | 2.4 |  | 2.4 |  |  |
|  |  |  | 4.5 | 3.6 |  |  | 3.6 |  | 3.6 |  |  |
|  |  |  | 5.5 | 4.4 |  |  | 4.4 |  | 4.4 |  |  |
| $\mathrm{V}_{\text {IL }}$ | Maximum Low-Level Input Voltage |  | 2.0 |  |  | 0.3 |  | 0.3 |  | 0.3 | V |
|  |  |  | 3.0 |  |  | 0.6 |  | 0.6 |  | 0.6 |  |
|  |  |  | 4.5 |  |  | 0.9 |  | 0.9 |  | 0.9 |  |
|  |  |  | 5.5 |  |  | 1.1 |  | 1.1 |  | 1.1 |  |
| V он | Minimum High-Level Output Voltage$\mathrm{V}_{\mathbb{I N}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}}$ | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {IH }}$ or $\mathrm{V}_{\text {IL }}$ | 2.0 | 1.9 | 2.0 |  | 1.9 |  | 1.9 |  | V |
|  |  | $\mathrm{I}_{\text {он }}=-50 \mu \mathrm{~A}$ | 3.0 | 2.9 | 3.0 |  | 2.9 |  | 2.9 |  |  |
|  |  |  | 4.5 | 4.4 | 4.5 |  | 4.4 |  | 4.4 |  |  |
|  |  | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {HH }}$ or $\mathrm{V}_{\text {IL }}$ |  |  |  |  |  |  |  |  |  |
|  |  | $\mathrm{I}_{\text {он }}=-4 \mathrm{~mA}$ | 3.0 | 2.58 |  |  | 2.48 |  | 2.34 |  |  |
|  |  | $\mathrm{I}_{\mathrm{OH}}=-8 \mathrm{~mA}$ | 4.5 | 3.94 |  |  | 3.80 |  | 3.66 |  |  |
| V oL | Maximum Low-Level Output Voltage $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\text {IH }}$ or $\mathrm{V}_{\mathrm{IL}}$ | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {H }}$ or $\mathrm{V}_{\text {IL }}$ | 2.0 |  | 0.0 | 0.1 |  | 0.1 |  | 0.1 | V |
|  |  | $\mathrm{I} \mathrm{oL}=50 \mu \mathrm{~A}$ | 3.0 |  | 0.0 | 0.1 |  | 0.1 |  | 0.1 |  |
|  |  |  | 4.5 |  |  | 0.1 |  | 0.1 |  | 0.1 |  |
|  |  | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {IH }}$ Or $\mathrm{V}_{\text {IL }}$ |  |  |  |  |  |  |  |  |  |
|  |  | $\mathrm{I}_{\mathrm{oL}}=4 \mathrm{~mA}$ | 3.0 |  |  | 0.36 |  | 0.44 |  | 0.52 |  |
|  |  | $\mathrm{I}_{\mathrm{oL}}=8 \mathrm{~mA}$ | 4.5 |  |  | 0.36 |  | 0.44 |  | 0.52 |  |
| $\mathrm{I}_{\text {IN }}$ | Maximum Input | $\mathrm{V}_{\text {IN }}=5.5 \mathrm{~V}$ or GND | 0 to5.5 |  |  | $\pm 0.1$ |  | $\pm 1.0$ |  | $\pm 1.0$ | $\mu \mathrm{A}$ |
|  | Leakage Current |  |  |  |  |  |  |  |  |  |  |
| I cc | Maximum Quiescent | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\text {cc }}$ or GND | 5.5 |  |  | 2.0 |  | 20 |  | 40 | $\mu \mathrm{A}$ |
|  | Supply Current |  |  |  |  |  |  |  |  |  |  |
|  |  |  |  |  |  |  |  |  |  |  |  |

AC ELECTRICAL CHARACTERISTICS $C_{\text {load }}=50 \mathrm{pF}$, Input $\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=3.0 \mathrm{~ns}$

6. $C_{\text {po }}$ is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{C C(O P R)}=C_{P D} \cdot V_{C C} \cdot f_{i n}+I_{C C} \cdot C_{P D}$ is used to determine the noload dynamic power consumption; $\mathrm{P}_{\mathrm{D}}=\mathrm{C}_{\mathrm{PD}} \cdot \mathrm{V}_{\mathrm{cc}}{ }^{2} \cdot \mathrm{f}_{\text {in }} \mathrm{I}_{\mathrm{CC}} \cdot \mathrm{V}_{\mathrm{cc}}$.

## MC74VHC1GU04



DEVICE ORDERING INFORMATION

| Device <br> Order Number | Device Nomenclature |  |  |  |  |  | Package Type (Name/SOT\#/ Common Name) | Tape and Reel Size |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Circuit Indicator | Temp <br> Range <br> Identifier | Technology | Device Function | Package Suffix |  <br> Reel <br> Suffix |  |  |
| MC74VHC1GU04DFT1 | MC | 74 | VHC1G | U04 | DF | T1 | $\begin{gathered} \hline \text { SC-70/SC-88A/ } \\ \text { SOT-353 } \end{gathered}$ | $\begin{gathered} 178 \mathrm{~mm}(7 \mathrm{in}) \\ 3000 \text { Unit } \end{gathered}$ |
| MC74VHC1GU04DFT2 | MC | 74 | VHC1G | U04 | DF | T2 | $\begin{gathered} \hline \text { SC-70/SC-88A/ } \\ \text { SOT-353 } \end{gathered}$ | $\begin{gathered} 178 \mathrm{~mm} \text { (7 in) } \\ 3000 \text { Unit } \end{gathered}$ |
| MC74VHC1GU04DFT4 | MC | 74 | VHC1G | U04 | DF | T4 | $\begin{gathered} \hline \text { SC-70/SC-88A/ } \\ \text { SOT-353 } \\ \hline \end{gathered}$ | $\begin{gathered} 330 \mathrm{~mm} \text { (13 in) } \\ 10,000 \text { Unit } \\ \hline \end{gathered}$ |
| MC74VHC1GU04DTT1 | MC | 74 | VHC1G | U04 | DT | T1 | SOT-23/TSOPS/ SC-59 | $\begin{gathered} 178 \mathrm{~mm}(7 \mathrm{in}) \\ 3000 \text { Unit } \end{gathered}$ |
| MC74VHC1GU04DTT3 | MC | 74 | VHC1G | U04 | DT | T3 | $\begin{gathered} \hline \text { SOT-23/TSOPS/ } \\ \text { SC-59 } \end{gathered}$ | $\begin{gathered} 330 \mathrm{~mm} \text { (13 in) } \\ 10,000 \text { Unit } \end{gathered}$ |

